

30 V, P-channel Trench MOSFET 25 March 2015

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Ultra thin package profile of 0.37 mm height

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quid	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-410	mA
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I _D = -410 mA; T _j = 25 °C		-	1.2	1.4	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

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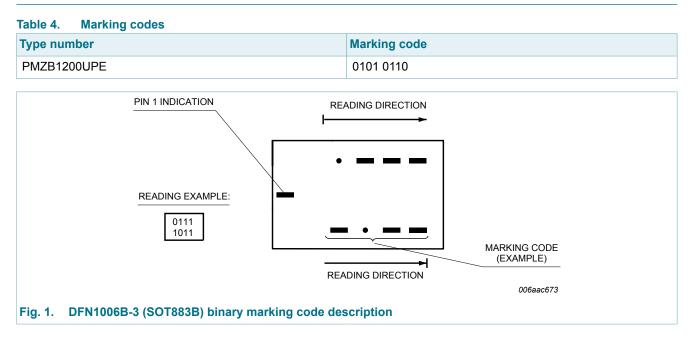
5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D
2	S	source	2	
3	D	drain	Transparent top view DFN1006B-3 (SOT883B)	G S 017aaa259

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PMZB1200UPE	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B				

7. Marking



8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C	[1]	-	-410	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-260	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-1.7	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	310	mW
			[1]	-	400	mW
		T _{sp} = 25 °C		-	1670	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-410	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

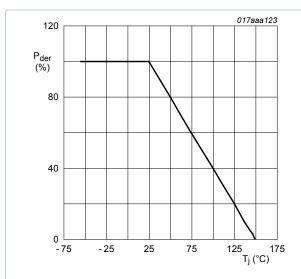


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

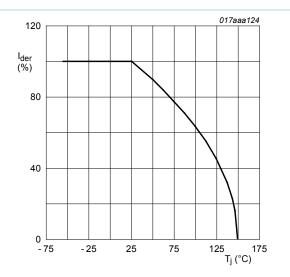
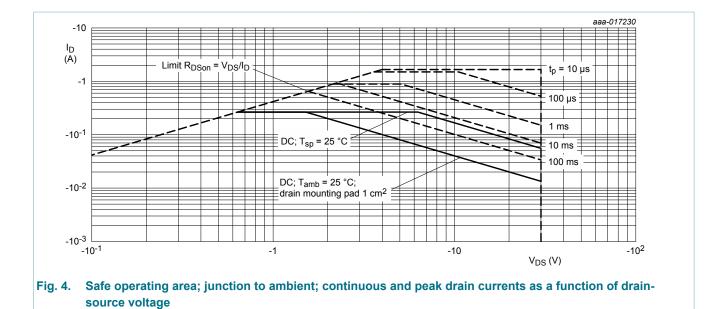


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^\circ \text{C})}} \times 100 \%$$

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9. Thermal characteristics

Table 6. Thermal characteristics

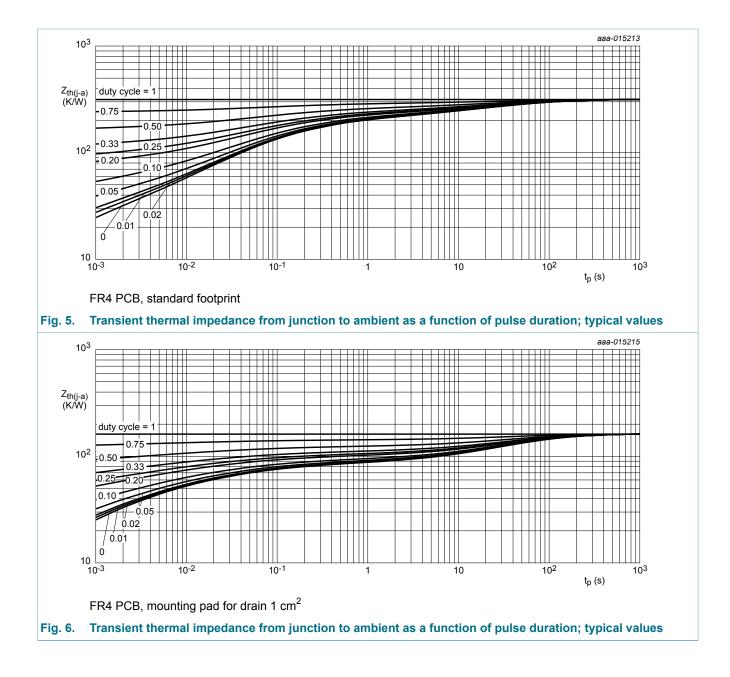
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
	thermal resistance	—	[1]	-	350	405	K/W
	from junction to ambient		[2]	-	270	310	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	65	75	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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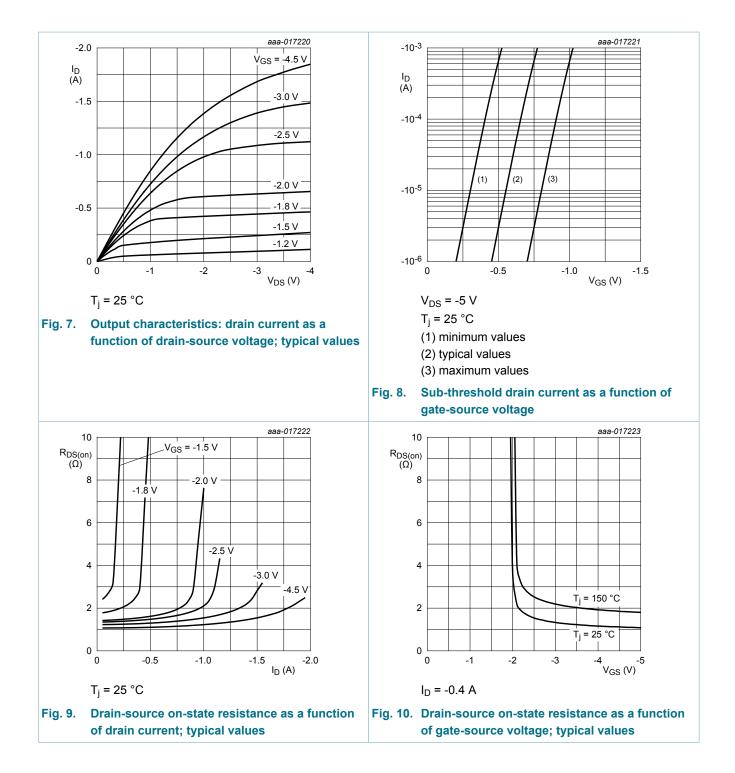


10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-30	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V_{DS} = -30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	nA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	nA
		V_{GS} = 2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -2.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-100	nA
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I _D = -410 mA; T _j = 25 °C	-	1.2	1.4	Ω
re	resistance	V _{GS} = -4.5 V; I _D = -410 mA; T _j = 150 °C	-	2	2.4	Ω
		V_{GS} = -2.5 V; I _D = -320 mA; T _j = 25 °C	-	1.7	2.3	Ω
		V _{GS} = -1.8 V; I _D = -80 mA; T _j = 25 °C	-	2.1	3.1	Ω
		V _{GS} = -1.5 V; I _D = -10 mA; T _j = 25 °C	-	3	5.1	Ω
9 _{fs}	forward transconductance	V_{DS} = -10 V; I _D = -200 mA; T _j = 25 °C	-	820	-	mS
Dynamic ch	aracteristics	· · · ·	I			
Q _{G(tot)}	total gate charge	V _{DS} = -15 V; I _D = -410 mA;	-	0.7	1.2	nC
Q _{GS}	gate-source charge	V _{GS} = -4.5 V; T _j = 25 °C	-	0.2	-	nC
Q _{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	43.2	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	5.9	-	pF
C _{rss}	reverse transfer capacitance		-	4.2	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -15 V; I _D = -410 A; V _{GS} = -4.5 V;	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t _{d(off)}	turn-off delay time	1	-	14	-	ns
t _f	fall time	1	-	5	-	ns
Source-drai	in diode				1	
V _{SD}	source-drain voltage	I _S = -410 mA; V _{GS} = 0 V; T _i = 25 °C	-	-0.95	-1.2	V

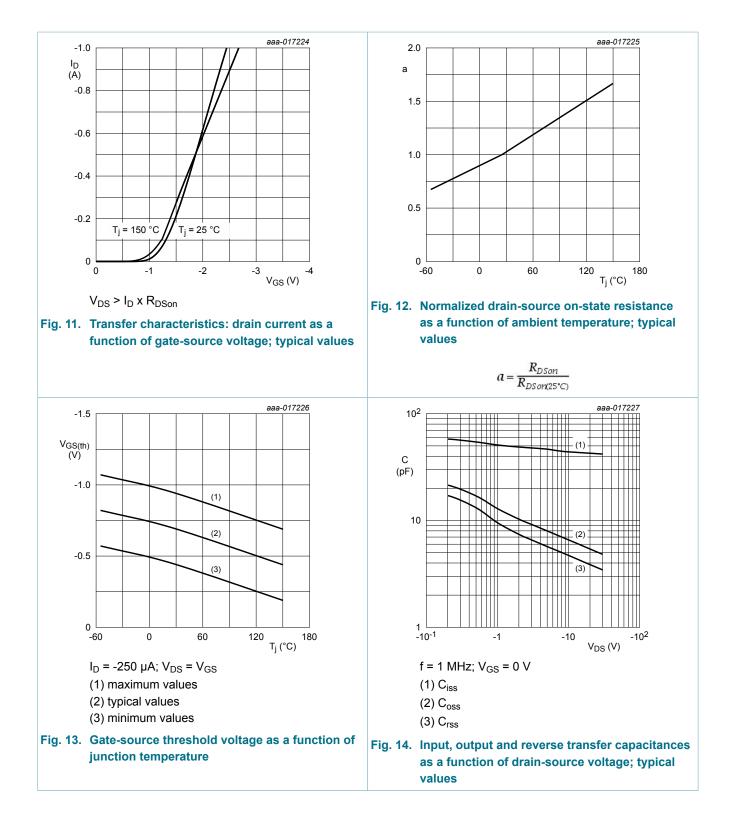
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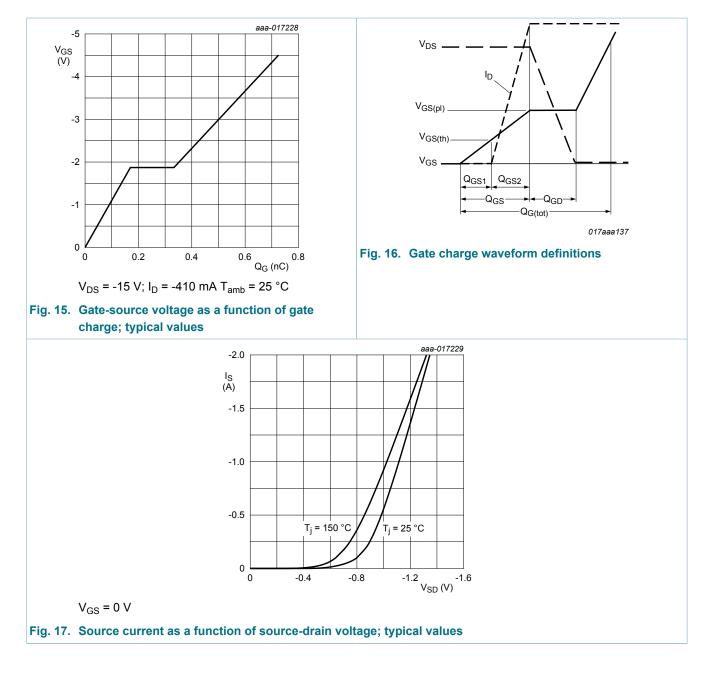
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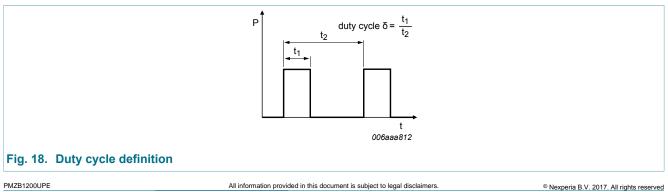
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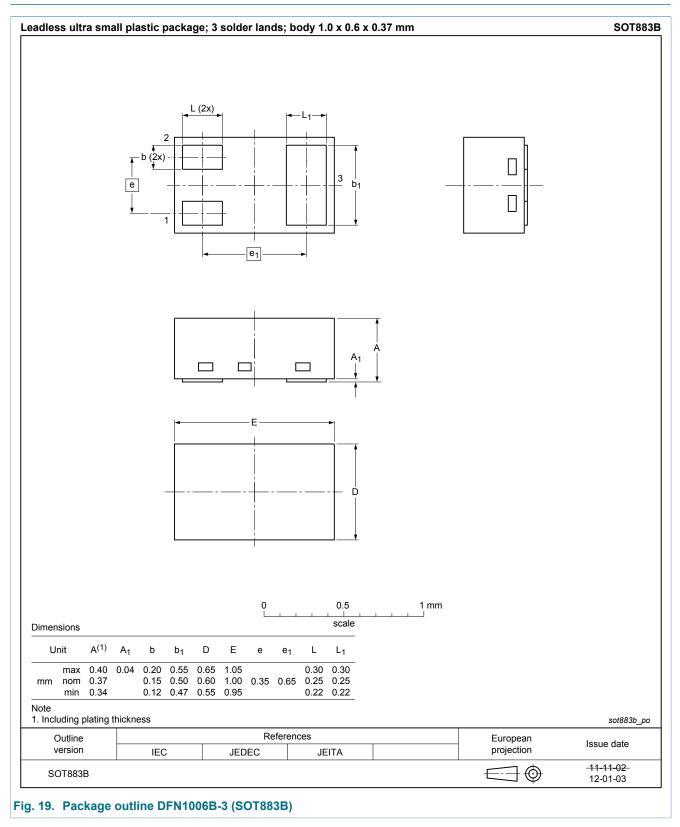
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11. Test information



12. Package outline



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13. Soldering

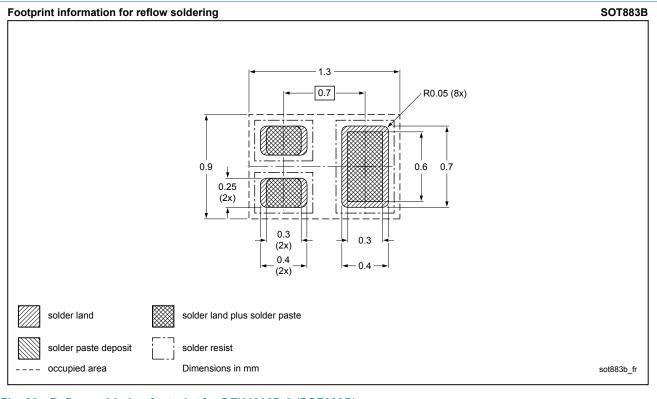


Fig. 20. Reflow soldering footprint for DFN1006B-3 (SOT883B)

14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMZB1200UPE v.1	20150325	Product data sheet	-	-		

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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